

**/ Descriptions**

TO-92LM          NPN          Silicon NPN transistor in a TO-92LM Plastic Package.

**/ Features**

2SB562  
Complementary pair with 2SB562.

**/ Applications**

Low frequency power amplifier.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Base          PIN 2 Collector          PIN 3 Emitter

**/  $h_{FE}$  Classifications & Marking**

$h_{FE}$ Classifications Symbol	B	C
$h_{FE}$ Range	85 170	120 240

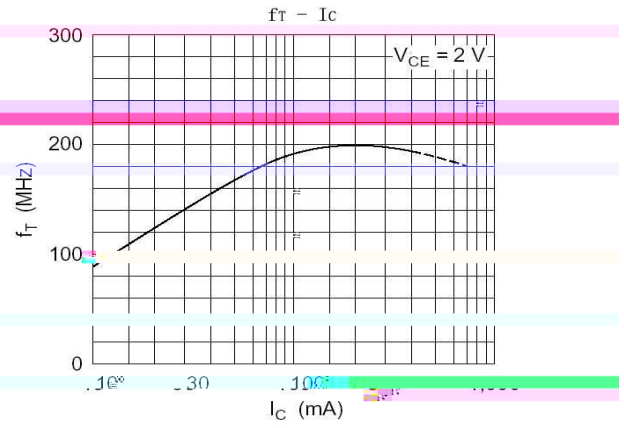
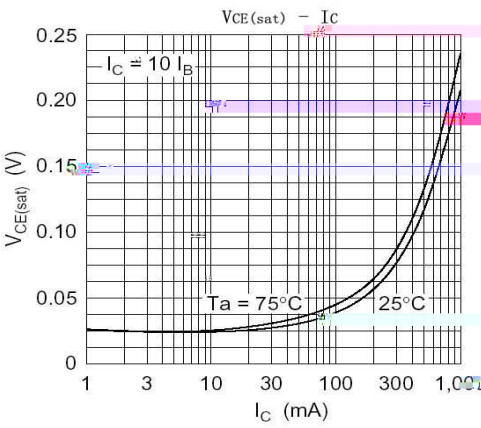
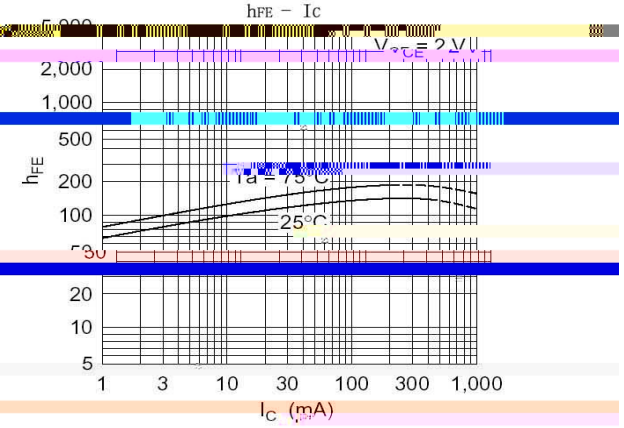
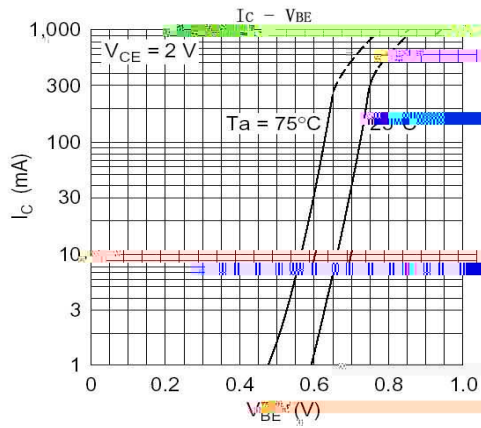
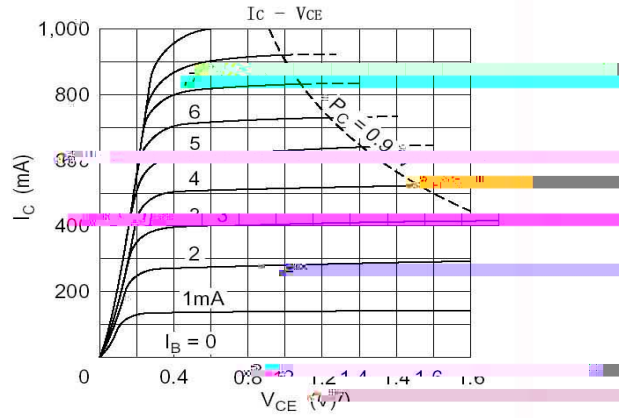
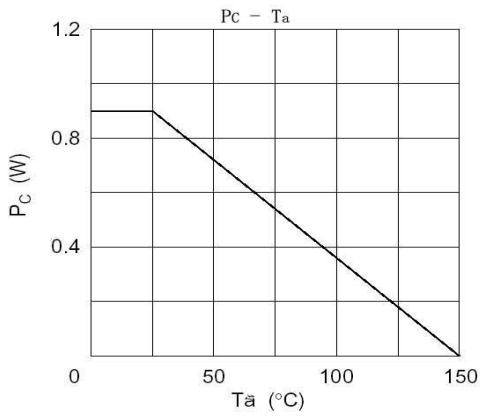
**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	25	V
Collector to Emitter Voltage	$V_{CEO}$	20	V
Emitter to Base Voltage	$V_{EBO}$	5.0	V
Collector Current (DC)	$I_C$	1.0	A
Collector Power Dissipation	$P_C$	900	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=10\mu A$ $I_E=0$	25			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0mA$ $R_{BE}=\infty$	20			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=10\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=20V$ $I_E=0$			1.0	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=2.0V$ $I_C=0.5A$	85		240	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.8A$ $I_B=0.08A$		0.2	0.5	V
Base to Emitter Voltage	$V_{BE}$	$V_{CE}=2.0V$ $I_C=0.5A$		0.79	1.0	V
Transition Frequency	$f_T$	$V_{CE}=2.0V$ $I_C=0.5A$		190		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		22		pF

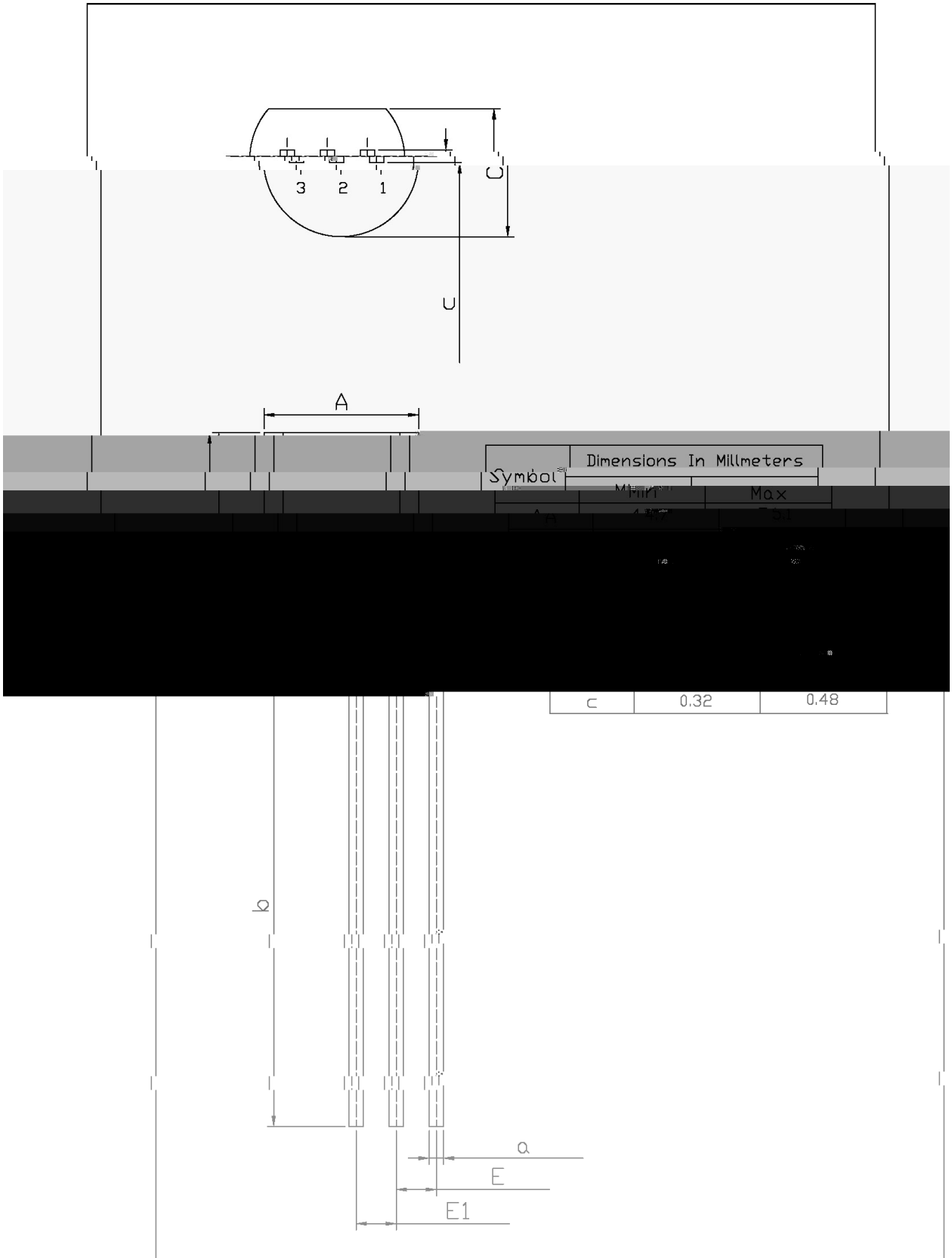
**/ Electrical Characteristic Curve**



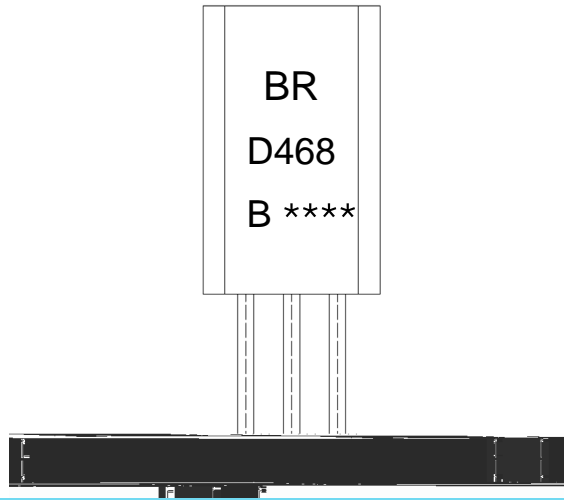
**/ Package Dimensions**

TO-92LM

Unit: mm



/ Marking Instructions



BR:

D468

B:                   h

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Note:

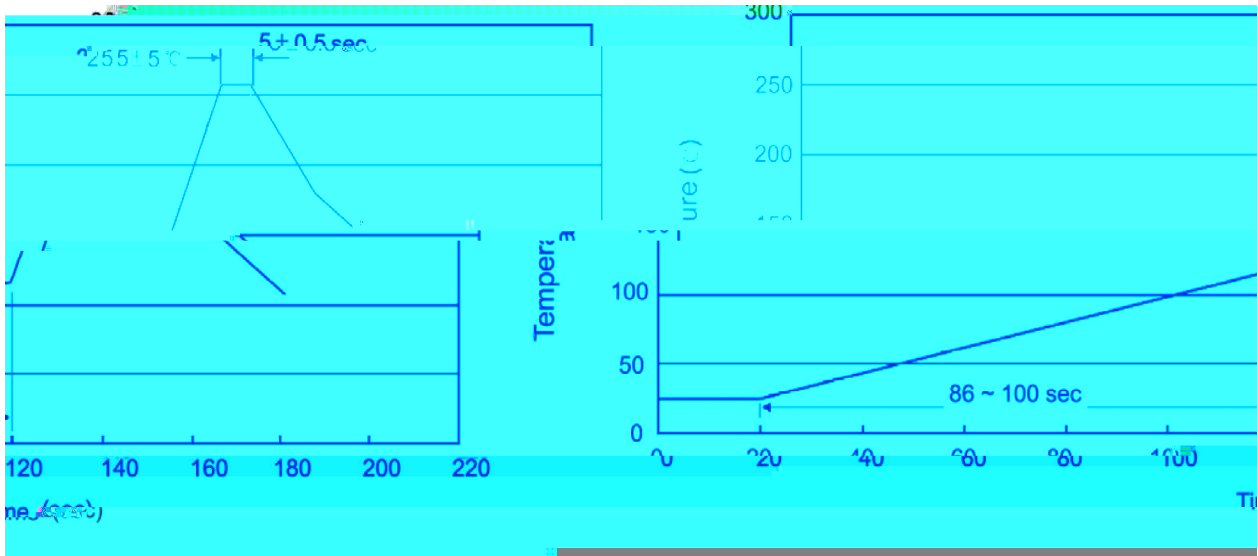
BR:                   Company Code.

D468:                Product Type.

B:                     $h_{FE}$  Classifications Symbol

\*\*\*\*:                Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1        25 150            60 90sec;
- 2        255±5                5±0.5sec;
- 3                    2 10 /sec.

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Tf0.56Db2fTj/TT2

1

Tf2

0

TD-0.0005;